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# TABLE OF CONTENTS

<p>PRELIMINARY RESULTS OF A NOVEL LOW VOLTAGE M-OTP IN MOS TRANSISTOR IN 28NM FD-SOI.....</p> <p style="padding-left: 20px;"><i>Ph. Galy, M. Bawedin, R. Lethiecq</i></p>	1
<p>A 64X1 FUSE MEMORY WITH 0.4V/1<math>\mu</math>A READ AND 0.9V PROGRAM VOLTAGE ON 22NM FD-SOI.....</p> <p style="padding-left: 20px;"><i>Shine Chung, Wen-Kuan Fang</i></p>	4
<p>A RERAM MEMORY COMPILER WITH LAYOUT-PRECISE PERFORMANCE EVALUATION.....</p> <p style="padding-left: 20px;"><i>Edward Lee, Daehyun Kim, Venkata Chaitanya Krishna Chekuri, Yun Long, Saibal Mukhopadhyay</i></p>	6
<p>MATERIALS REQUIREMENTS OF HIGH-SPEED AND LOW-POWER SPIN-ORBIT- TORQUE MAGNETIC RANDOM-ACCESS MEMORY.....</p> <p style="padding-left: 20px;"><i>Xiang Li, Shy-Jay Lin, Dc Mahendra, Yu-Ching Liao, Chengyang Yao, Azad Naeemi, Wilman Tsai, Shan X. Wang</i></p>	9
<p>THERMAL NOISE-INDUCED ERROR SIMULATION FRAMEWORK FOR SUBTHRESHOLD CMOS SRAM.....</p> <p style="padding-left: 20px;"><i>Elahe Rezaei, Marco Donato, William Patterson, Alexander Zaslavsky, R. Iris Bahar</i></p>	12
<p>A RING OSCILLATOR USING BOOTSTRAP INVERTER.....</p> <p style="padding-left: 20px;"><i>Akinori Yamamoto, Trong-Thuc Hoang, Cong-Kha Pham</i></p>	15
<p>FROM 180NM TO 7NM: CROSSTALK COMPUTING SCALABILITY STUDY.....</p> <p style="padding-left: 20px;"><i>Md Arif Iqbal, Naveen Kumar Macha, Bhavana Tejaswini Repalle, Mostafizur Rahman</i></p>	17
<p>IMPROVING DYNAMIC LEAKAGE SUPPRESSION LOGIC WITH FORWARD BODY BIAS IN 65NM CMOS.....</p> <p style="padding-left: 20px;"><i>Daniel S. Truesdell, Benton H. Calhoun</i></p>	19
<p>TCAD-SPICE CO-SIMULATION OF FERROELECTRIC CAPACITOR AS AN ELECTRICALLY TRIMMABLE ON-CHIP CAPACITOR IN ANALOG CIRCUIT.....</p> <p style="padding-left: 20px;"><i>K. Huynh, A. C. Tenkeu, K. P. Pun, H. Y. Wong</i></p>	21
<p>22FDX<sup>®</sup> EMBRACING IOT, 5G, AND AUTOMOTIVE APPLICATIONS - A PERSPECTIVE THROUGH GLOBAL RESEARCH.....</p> <p style="padding-left: 20px;"><i>Qiang Brian Chen, Jamie K. Schaeffer</i></p>	24
<p>ADVANCED 22 NM FD-SOI DEVICES INTEGRATION PLATFORM.....</p> <p style="padding-left: 20px;"><i>Ming Tian, Cuiqin Xu, Haibo Lei</i></p>	29
<p>HIGH BRIGHTNESS AND BONDING YIELD OF INTEGRATED SI-CMOS AND GAN LED WAFERS.....</p> <p style="padding-left: 20px;"><i>Kwang Hong Lee, Lin Zhang, Li Zhang, Yue Wang, Kenneth Eng Kian Lee, Soo Jin Chua, Eugene A. Fitzgerald, Chuan Seng Tan</i></p>	33
<p>HETEROGENEOUS MICRO LED DISPLAYS YIELD STATISTICS.....</p> <p style="padding-left: 20px;"><i>Khaled Ahmed</i></p>	36

MICROFLUIDIC COOLING FOR 3D-IC WITH 3D PRINTING PACKAGE.....	38
<i>Jun-Han Han, Karina Torres-Castro, Robert E. West, Walter Varhue, Nathan Swami, Mircea Stan</i>	
POTENTIAL OF A NOVEL DOUBLE-SIDED FULLY-DEPLETED SILICON-ON-INSULATOR CMOS ARCHITECTURE FOR THE NEXT-GENERATION MONOLITHIC 3D CPUS AND SOCS .....	41
<i>Ahmad Houssam Tarakji, Nirmal Chaudhary</i>	
150-NW FD-SOI INTERMITTENT STARTUP CIRCUIT FOR MICROPOWER ENERGY HARVESTING SENSOR .....	44
<i>Minoru Sudo, Fumiyasu Utsunomiya, Ami Tanaka, Takayuki Douseki</i>	
A 0.75-V 58-MHZ 340- $\mu$ W SOTB-65NM 32-POINT DCT IMPLEMENTATION BASED ON FIXED-ROTATION ADAPTIVE CORDIC.....	46
<i>Ngoc-Tu Bui, Trong-Thuc Hoang, Akinori Yamamoto, Duc-Hung Le, Cong-Kha Pham</i>	
FEMTOAMPERE SENSITIVE CURRENT MEASUREMENT ASIC IN 22 NM TECHNOLOGY.....	49
<i>Sarath Kundumattathil Mohanan, Hamza Boukabache, Daniel Perrin, Ullrich Pfeiffer</i>	
A 23 GHZ VCO WITH 13% FTR IN 22 NM FDSOI.....	52
<i>Piyush Kumar, Jidan Al-Eryani, David Borggreve, Enno Böhme, Pragoti Pran Bora, Erkan Nevzat Isa, Linus Maurer</i>	
A 9PW/BIT 400MV 3T GAIN-CELL EDRAM FOR ULP APPLICATIONS IN 28 NM FD-SOI.....	55
<i>Amir Shalom, Alexander Fish, Adam Teman</i>	
GROUP IV/OXIDE SEMICONDUCTOR BI-LAYER TUNNELING FET .....	57
<i>Shinichi Takagi, Kimihiko Kato, Mitsuru Takenaka</i>	
NEW PRE-REQUISITES FOR STEEP SUB-THRESHOLD TUNNEL TRANSISTORS .....	60
<i>Sri Krishna Vadlamani, Sapan Agarwal, Eli Yablonovitch</i>	
TWO-STAGE AMPLIFIER DESIGN BASED ON EXPERIMENTAL LINE-TUNNEL FET DATA.....	63
<i>Walter Gonçalez Filho, Joao A. Martino, Roberto Rangel, Paula G. D. Agopian, Eddy Simoen, Rita Rooyackers, Cor Claeys, Nadine Collaert</i>	
IMPACT OF ON-CURRENT ON THE STATIC AND DYNAMIC PERFORMANCE OF TFET INVERTERS .....	66
<i>Atieh Farokhnejad, Fabian Horst, Alexander Kloes, Benjamín Iñíguez, François Lime</i>	
CARRIER MOBILITY VARIATION INDUCED BY THE SUBSTRATE BIAS IN $\Omega$ -GATE SOI NANOWIRE MOSFETS .....	68
<i>F. E. Bergamaschi, T. A. Ribeiro, B. C. Paz, M. De Souza, S. Barraud, M. Cassé, M. Vinet, O. Faynot, M. A. Pavanello</i>	
SI LAYERS TRANSFER ON SAPPHIRE OR SILICON WITH HIGH-K STACK OF PEALD DIELECTRIC NANOLAYERS.....	71
<i>Vladimir Popov, Valentin Antonov, Alexey Leushin, Ida Tyschenko, Anton Gutakovskiy, Andrey Miakonkich, Konstantin Rudenko</i>	
CHARGE TRAP LAYER (CTL) SOI SUBSTRATES USING FLOAT ZONE WAFERS ACHIEVING LOW SUBSTRATE LOSSES.....	73
<i>Jeffrey Libbert, Leif Jensen, Theis Leth Sveigaard, Mike Seacrist, Carissima Hudson, Shawn G. Thomas</i>	

QUANTITATIVE EVALUATION OF MOBILITY SCATTERING MECHANISMS IN ULTRA-THIN-BODY GE-OI PMOSFETS .....	75
<i>Sicong Yuan, Walter Schwarzenbach, Zhuo Chen, Bich-Yen Nguyen, Rui Zhang</i>	
POTENTIAL WELL BASED FDSOI MOSFET: A NOVEL PLANAR DEVICE FOR 10 NM GATE LENGTH .....	77
<i>Shafi Qureshi, Shruti Mehrotra</i>	
HIGH BREAKDOWN VOLTAGE MESFETS INTEGRATED WITH SOI CMOS TECHNOLOGIES.....	80
<i>Trevor Thornton</i>	
A BENCHMARK STUDY OF COMPLEMENTARY-FIELD EFFECT TRANSISTOR (CFET) PROCESS INTEGRATION OPTIONS: COMPARING BULK VS. SOI VS. DSOI STARTING SUBSTRATES.....	81
<i>Benjamin Vincent, J. Ervin, J. Boemmels, J. Ryckaert</i>	
STATISTICAL CHARACTERIZATION AND MODELLING OF GATE-INDUCED DRAIN LEAKAGE VARIABILITY IN ADVANCED FDSOI DEVICES.....	83
<i>T. A. Karatsori, C. Cavalcante, J. Lacord, P. Batude, C. Theodorou, G. Ghibaudo</i>	
POWER AND VARIATION IMPROVED NEAR-VT STANDARD CELL LIBRARY FOR 28-NM FDSOI.....	85
<i>Wing-Tsi Wong, Kamlesh Singh, Jos Huisken, José Pineda De Gyvez</i>	
VOLTAGE STACKING FOR NEAR/SUB-THRESHOLD ULTRA-LOW POWER MICROPROCESSOR SYSTEMS .....	87
<i>Kamlesh Singh, Barry De Bruin, Jos Huisken, Hailong Jiao, Henk Corporaal, José Pineda De Gyvez</i>	
NEW DESIGN PRINCIPLES FOR COLD ELECTRONICS.....	89
<i>Erik P. Debenedictis, Michael P. Frank</i>	
METHODOLOGY FOR DEFINING THE CHARACTERIZATION CORNERS OF FOUNDATION IPS AND HARD MACROS IN AN ADAPTIVE BODY-BIASED CONTROLLED AREA.....	91
<i>Mathieu Louvat, Andrea Bonzo, Anthony Mialon, Philippe Flatresse, Sebastien Genevey, Lionel Jure, Vincent Huard</i>	
PERFORMANCE ENHANCEMENT OF 4T-IFGC DRAM IN 7NM NC-FINFET TECHNOLOGY NODE.....	94
<i>Koshal Sharma, Amol D. Gaidhane, Yogesh Singh Chauhan</i>	
A 28GHZ SPDT TRX SWITCH WITH 9KV ESD PROTECTION IN 22NM SOI CMOS FOR 5G MOBILES .....	96
<i>Feilong Zhang, Cheng Li, Chenkun Wang, Mengfu Di, Zijin Pan, David Harame, Albert Wang</i>	
BURIED OXIDE ON EXTENDED DRAIN MOSFET (BOX EDMOS) FOR RF APPLICATIONS IN FDSOI/BULK TECHNOLOGY .....	98
<i>Aliaksei Ivaniukovich, Kwanyoung Kim, Wooyeol Maeng, Huichul Shin, Kangwook Park, Yoon-Suk Kim, Uihui Kwon, Dae Sin Kim</i>	
LINEAR AND EFFICIENT NFET-MESFET 5G CASCODE POWER AMPLIFIERS USING 45NM SOI CMOS.....	101
<i>Trevor J. Thornton, Chaojiang Li, Payam Mehr</i>	

28 FDSOI RF FIGURES OF MERIT DOWN TO 4.2 K .....	103
<i>L. Nyssens, A. Halder, B. Kazemi Esfeh, N. Planes, D. Flandre, V. Kilchytska, J.-P. Raskin</i>	
A 3.2–3.6GHZ SOI-LDMOS DUAL-INPUT DOHERTY POWER AMPLIFIER .....	106
<i>Saad Boutayeb, Ayssar Serhan, Pascal Reynier, Damien Parat, Alexis Divay, Jean-Daniel Arnould, Estelle Lauga-Larroze, Alexandre Giry</i>	
HFZRO FERROELECTRIC CHARACTERIZATION AND PARAMETERIZATION OF RESPONSE TO ARBITRARY EXCITATION WAVEFORM.....	108
<i>Md Nur K. Alam, M. Thesberg, B. Kaczer, Ph. Roussel, B. Vermeulen, B. Truijen, M. I. Popovici, L.-å Ragnarsson, A. S. Verhulst, N. Horiguchi, M. Heyns, J. Van Houdt</i>	
EVALUATING NEGATIVE CAPACITANCE TECHNOLOGY FOR RF MOS VARACTORS .....	111
<i>Girish Pahwa, Amit Agarwal, Yogesh Singh Chauhan</i>	
COMPARATIVE ANALYSIS OF NEGATIVE CAPACITANCE JUNCTIONLESS AND INVERSION MODE TRANSISTORS FOR LOW POWER APPLICATIONS .....	114
<i>Manish Gupta, Vita Pi-Ho Hu</i>	
ADVANCES IN 3D HETEROGENEOUS STRUCTURES AND INTEGRATION FOR FUTURE ICS (INVITED).....	116
<i>Cheng Li, Feilong Zhang, Mengfu Di, Zijin Pan, Albert Wang</i>	
TRIPLE-STACKED SILICON-ON-INSULATOR INTEGRATED CIRCUITS USING AU/SIO <sub>2</sub> HYBRID BONDING .....	119
<i>Yuki Honda, Masahide Goto, Toshihisa Watabe, Masakazu Nanba, Yoshinori Iguchi, Takuya Saraya, Masaharu Kobayashi, Eiji Higurashi, Hiroshi Toshiyoshi, Toshiro Hiramoto</i>	
TSV WITH EMBEDDED CAPACITOR FOR ASIC-HBM POWER AND SIGNAL INTEGRITY IMPROVEMENT.....	122
<i>Anak Agung Alit Apriyana, Lin Ye, Tan Chuan Seng</i>	
HETEROGENEOUS MULTI-DIMENSIONAL INTEGRATED CIRCUIT FOR INTERNET-OF- THINGS APPLICATION .....	124
<i>Nazek El-Atab, Sohail F. Shaikh, Sherjeel Khan, Joho Yun, Muhammad Mustafa Hussain</i>	
LOW-FREQUENCY NOISE TRANSISTOR PERFORMANCE FOR UTBB FDSOI MOSFET-C FILTERS .....	126
<i>L. Van Brandt, B. Kazemi Esfeh, N. Planes, V. Kilchytska, D. Flandre</i>	
SUBTHRESHOLD OPERATION OF SELF-CASCADE STRUCTURE USING UTBB FD SOI PLANAR MOSFETS .....	128
<i>Lígia Martins D'Oliveira, Valeriya Kilchytska, Nicolas Planes, Denis Flandre, Michelly De Souza</i>	
DEGRADATION OF SUB-THRESHOLD SLOPE IN ULTRA-SCALED MOSFETS DUE TO ENERGY FILTERING AT SOURCE CONTACT.....	131
<i>J. Saltin, N. C. Dao, P. H. W. Leong, H. Y. Wong</i>	
OPTIMIZATION OF PHOTOELECTRON IN-SITU SENSING DEVICE IN FD-SOI.....	134
<i>J. Liu, M. Arsalan, A. Zaslavsky, S. Cristoloveanu, J. Wan</i>	
SOFT ERROR TOLERANCE OF STANDARD AND STACKED LATCHES DEPENDENDING ON SUBSTRATE BIAS IN A FDSOI PROCESS EVALUATED BY DEVICE SIMULATION.....	136
<i>Kentaro Kojima, Jun Furuta, Kazutoshi Kobayashi</i>	

EFFECT OF $V_{SUB}$ AND POSITIVE CHARGE IN BURIED OXIDE ON SUPER STEEP SS “PN BODY-TIED SOI-FET” AND PROPOSAL OF CMOS WITHOUT $V_{SUB}$ BIAS .....	139
<i>Wataru Yabuki, Jiro Ida, Takayuki Mori, Koichiro Ishibashi, Yasuo Arai</i>	
CRYSTAL GROWTH STUDY OF THE GRAIN-BOUNDARY FREE (100) TEXTURED SI THIN-FILMS BY USING THE CW-LASER LATERAL CRYSTALLIZATION .....	142
<i>Nobuo Sasaki, Muhammad Arif, Yukiharu Uraoka, Jun Gotoh, Shigeto Sugimoto</i>	
LASER PROCESSING FOR 3D JUNCTIONLESS TRANSISTOR FABRICATION.....	144
<i>D. Bosch, P. Acosta Alba, S. Kerdiles, V. Benevent, C. Perrot, J. Lassarre, J. Richey, J. Lacord, B. Sklenard, L. Brunet, P. Batude, C. Fenouillet-Béranger, D. Lattard, J. P. Colinge, F. Balestra, F. Andrieu</i>	
DOUBLE SOI SUBSTRATES FOR ADVANCED TECHNOLOGIES .....	147
<i>W. Schwarzenbach, G. Besnard, G. Chabanne, B.-Y. Nguyen</i>	
MTJ-BASED NONVOLATILE LOGIC-IN-MEMORY CIRCUIT WITH FEEDBACK-TYPE EQUAL-RESISTANCE SENSING MECHANISM FOR TERNARY NEURAL NETWORK HARDWARE.....	149
<i>Masanori Natsui, Takahiro Hanyu</i>	
DESIGN AND STUDY OF AN ARTIFICIAL SPIKING NEURON ENABLED BY LOW-VOLTAGE $SiO_x$ -BASED RERAM .....	151
<i>Jessie Xuhua Niu, Yida Li, Hasita Veluri, Aaron Voon-Yew Thean</i>	
MIXED-SIGNAL NEUROMORPHIC PROCESSORS: QUO VADIS?.....	154
<i>Mohammad Bavandpour, Mohammad Reza Mahmoodi, Shubham Sahay, Dmitri B. Strukov</i>	
IMPACT OF FURNACE ANNEALING AND OTHER PROCESS FAILURES TO BE TAKEN CARE DURING FABRICATION OF AN ALGAN/GAN MOSHEMT .....	156
<i>Arathy Varghese, Chinnamuthan Periasamy, Lava Bhargava</i>	
OPTIMIZATION OF THE BACK ENHANCED $^{BE}$ SOI MOSFET WORKING AS A CHARGE-BASED BIOFET SENSOR.....	158
<i>L. S. Yojo, R. C. Rangel, K. R. A. Sasaki, C. A. Mori, J. A. Martino</i>	
INVESTIGATING THE SCALABILITY OF NANOWIRE JUNCTIONLESS ACCUMULATION MODE FETS USING AN INTRINSIC POCKET .....	161
<i>Aakash Kumar Jain, Jaspreet Singh, Mamidala Jagadesh Kumar</i>	
A PHYSICAL MODELING STUDY OF MOBILITY ENHANCEMENT IN STRESSED GE-ON-INSULATOR PMOSFET .....	164
<i>Haoqing Xu, Guilei Wang, Jiaxin Yao, Huaxiang Yin, Henry Radamson, Zhenhua Wu</i>	
PHYSICAL ANALYSIS OF NON-MONOTONIC DIBL DEPENDENCE ON BACK GATE BIAS IN THICK FRONT GATE OXIDE FDSOI MOSFETS .....	167
<i>Chetan Kumar Dabhi, Pragya Kushwaha, Harshit Agarwal, Sarvesh S. Chauhan, Chenming Hu, Yogesh Singh Chauhan</i>	
HIGH TEMPERATURE RELIABILITY STUDIES OF INNOVATIVE FUSE PROGRAMMING MODE.....	170
<i>Shine Chung, Wen-Kuan Fang, Michael Wendt, Heng-Kah Lee</i>	
A LINE TFET DESIGN EMPLOYING TRI-LINE-GATE ARCHITECTURE AND U-SHAPED POCKETS FOR MINIMIZING DRAIN FIELD EFFECTS.....	172
<i>Ashita, Sajad A. Loan, Mohammad Rafat</i>	

IMPACT OF GATE OXIDE TRAPS AND $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ /BOX TRAPS ON THE PERFORMANCE OF $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ ON INSULATOR TFET AND ITS MITIGATION .....	175
<i>Mohd Haris, Sajad Loan, Mainuddin</i>	
MODELING THE QUANTUM GATE CAPACITANCE OF NANO-SHEET GATE-ALL-AROUND MOSFET .....	178
<i>Pragya Kushwaha, Harshit Agarwal, Varun Mishra, Avirup Dasgupta, Yen-Kai Lin, Ming-Yen Kao, Yogesh Singh Chauhan, Sayeef Salahuddin, Chenming Hu</i>	
EDGE INFERENCE WITH NEM RELAYS .....	181
<i>Rawan Naous, Vladimir Stojanovic</i>	
TFET BASED 1T-DRAM: PHYSICS, SIGNIFICANCE AND TRADE-OFFS .....	183
<i>Nupur Navlakha, Md. Hasan Raza Ansari, Abhinav Kranti</i>	
OTA PERFORMANCE COMPARISON DESIGNED WITH EXPERIMENTAL NW-MOSFET AND NW-TFET DEVICES .....	186
<i>Alexandro De M. Nogueira, Paula G. D. Agopian, Roberto Rangel, Joao A. Martino, Eddy Simoen, Rita Rooyackers, Cor Claeys, Nadine Collaert</i>	
STUDY OF LAYOUT DEPENDENT RADIATION HARDNESS OF FINFET SRAM USING FULL DOMAIN 3D TCAD SIMULATION .....	189
<i>Khoa Huynh, Johan Saltin, Jin-Woo Han, Meyya Meyyappan, Hiu Yung Wong</i>	
DESIGN AND SIMULATION OF HIGH PERFORMANCE DOPINGLESS TUNNEL DIODE .....	192
<i>Faisal Bashir, Asim Majeed, Farooq A Khanday, M. Tariq Bandy</i>	
NEGATIVE CAPACITANCE GAN HEMT WITH IMPROVED SUBTHRESHOLD SWING AND TRANSCONDUCTANCE .....	195
<i>Km. Zhu, Jh. Wei, J. Wan</i>	
P-TYPE NEGATIVE CAPACITANCE FINFET WITH SUBTHRESHOLD CHARACTERISTICS AND DRIVING CURRENT IMPROVEMENT .....	197
<i>Zhaohao Zhang, Qingzhu Zhang, Zhaozhao Hou, Gaobo Xu, Qiuxia Xu, Huilong Zhu, Huxiang Yin</i>	
IMPROVED ELECTRICAL CHARACTERISTICS OF P-TYPE TUNNEL FIELD-EFFECT TRANSISTOR WITH SOURCE-POCKET JUNCTION FORMED USING HIGH-ANGLE IMPLANTATION .....	199
<i>Gaobo Xu, Huaxiang Yin, Qiuxia Xu, Guilong Tao, Guoliang Tian, Zhihao Li, Jinshun Bi, Jianhui Bu, Zhenhua Wu, Qingzhu Zhang, Yongliang Li, Jinbiao Liu, Junfeng Li, Huilong Zhu, Chao Zhao, Wenwu Wang</i>	
CHARACTERIZATION CHALLENGES AND SOLUTIONS FOR FDSOI TECHNOLOGIES .....	202
<i>Tomasz Brozek, Meindert Lunenburg, Franck Arnaud, Roberto Gonella, Jean-Christophe Giraudin, Christian Dutto, Bertrand Martinet, Laurent Garchery, Christopher Hess, Kelvin Doong</i>	

## Author Index